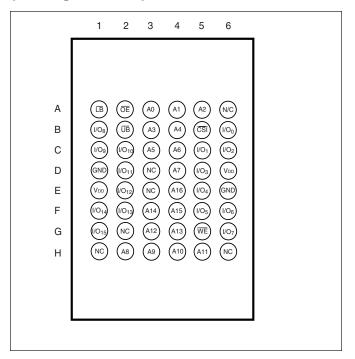
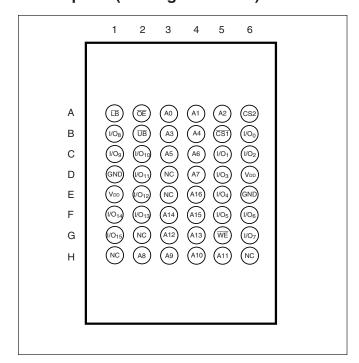


#### **PIN CONFIGURATIONS**

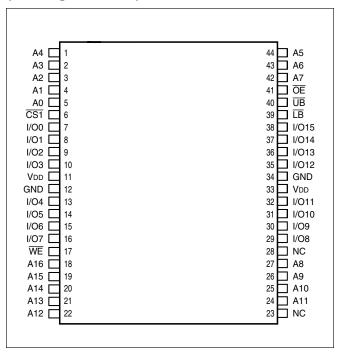
# 48-Pin mini BGA (6mm x 8mm) (Package Code B)



## 48-Pin mini BGA (6mm x 8mm) 2 CS Option (Package Code B2)



# 44-Pin mini TSOP (Type II) (Package Code T)



#### **PIN DESCRIPTIONS**

A0-A16	Address Inputs
I/O0-I/O15	Data Inputs/Outputs
<u>CS1</u> , CS2	Chip Enable Input
ŌĒ	Output Enable Input
WE	Write Enable Input
ĪB	Lower-byte Control (I/O0-I/O7)
<del>UB</del>	Upper-byte Control (I/O8-I/O15)
NC	No Connection
VDD	Power
GND	Ground



#### TRUTH TABLE

	·						I/O	PIN	
Mode	WE	CS <sub>1</sub>	CS2	<b>OE</b>	LB	<b>UB</b>	1/00-1/07	I/O8-I/O15	Vdd Current
Not Selected	Х	Н	Х	Х	Χ	Х	High-Z	High-Z	ISB1, ISB2
	Χ	X	L	Χ	Χ	Χ	High-Z	High-Z	ISB1, ISB2
	Χ	Χ	X	Χ	Н	Н	High-Z	High-Z	ISB1, ISB2
Output Disabled	Н	L	Н	Н	L	Х	High-Z	High-Z	lcc
	Н	L	Н	Н	Χ	L	High-Z	High-Z	Icc
Read	Н	L	Н	L	L	Н	<b>D</b> оυт	High-Z	lcc
	Н	L	Н	L	Н	L	High-Z	Dout	
	Н	L	Н	L	L	L	Dout	Dout	
Write	L	L	Н	Χ	L	Н	DIN	High-Z	lcc
	L	L	Н	Χ	Н	L	High-Z	DIN	
	L	L	Н	Χ	L	L	DIN	DIN	

#### ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit	
VTERM	Terminal Voltage with Respect to GND	-0.2 to V <sub>DD</sub> +0.3	V	
Тѕтс	Storage Temperature	-65 to +150	°C	
Рт	Power Dissipation	1.0	W	

#### Note:

# **OPERATING RANGE (VDD)**

Option	Ambient Temperature	IS65WV12816ALL	IS65WV12816BLL	
Α	0°C to +70°C	1.65V - 2.2V	2.5V - 3.6V	
A1	-40°C to +85°C	1.65V - 2.2V	2.5V - 3.6V	
A2	-40°C to +105°C	1.65V - 2.2V	2.5V - 3.6V	
A3	-40°C to +125°C	1.65V - 2.2V	2.5V - 3.6V	

Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a
stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational
sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect
reliability.



# DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	Vdd	Min.	Max.	Unit
Vон	Output HIGH Voltage	Iон = -0.1 mA	1.65-2.2V	1.4	_	V
	,	IOH = -1  mA	2.5-3.6V	2.2	_	V
Vol	Output LOW Voltage	IoL = 0.1 mA	1.65-2.2V	_	0.2	V
	-	lol = 2.1  mA	2.5-3.6V	_	0.4	V
VIH	Input HIGH Voltage		1.65-2.2V	1.4	V <sub>DD</sub> + 0.2	V
			2.5-3.6V	2.2	$V_{DD} + 0.3$	V
VIL <sup>(1)</sup>	Input LOW Voltage		1.65-2.2V	-0.2	0.4	V
			2.5-3.6V	-0.2	0.6	V
ILI	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$		-1	1	μΑ
ILO	Output Leakage	GND ≤ Vout ≤ Vdd, O	utputs Disabled	<b>-</b> 1	1	μΑ

#### Notes:

#### CAPACITANCE(1)

Symbol	Parameter	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 0V	8	pF
Соит	Input/Output Capacitance	Vout = 0V	10	pF

<sup>1.</sup>  $V_{IL}$  (min.) = -1.0V for pulse width less than 10 ns.

<sup>1.</sup> Tested initially and after any design or process changes that may affect these parameters.



# IS65WV12816ALL, POWER SUPPLY CHARACTERISTICS<sup>(1)</sup> (Over Operating Range)

Symbol	Parameter	<b>Test Conditions</b>	Options	Max. -70 ns	Unit
lcc	Vdd Dynamic Operating Supply Current	VDD=Max., IOUT=0 mA, f=fmax	A,A1 A2,A3	15 20	mA
lcc1	Operating Supply Current	VDD=Max., IOUT=0 mA, f=0	A, A1 A2, A3	7 7	mA
ISB1	TTL Standby Current (TTL Inputs)	VDD=Max., VIN=VIHORVIL CS1 = VIH, CS2=VIL, f = 1 MHz OR	A,A1 A2,A3	0.6 0.6	mA
	ULB Control	$\frac{V_{DD}=Max., V_{IN}=V_{IH} \text{ or } V_{IL}}{CS1}=V_{IL}, f=0, \overline{UB}=V_{IH}, \overline{LB}}$	=VIH		
ISB2	CMOS Standby Current (CMOS Inputs)	$\label{eq:decomposition} \begin{split} & \frac{\text{VDD=Max.,}}{\text{CS1}} \geq \text{VDD-0.2V,} \\ & \text{CS2} \leq 0.2\text{V,} \\ & \text{VIN} \geq \text{VDD-0.2V,or} \\ & \text{VIN} \leq 0.2\text{V,f} = 0 \end{split}$	A,A1 A2 A3	15 20 50	μΑ
	ULB Control	$V_{DD} = Max., \overline{CS1} = V_{IL}, V_{IN} \le 0.2V, f = 0; \overline{UB}/\overline{LB} = V_{D}$			

#### IS65WV12816BLL, POWER SUPPLY CHARACTERISTICS(1) (Over Operating Range)

Symbol	Parameter	<b>Test Conditions</b>	Options	Max. -55 ns	Max. -70 ns	Unit
lcc	Vdd Dynamic Operating	V <sub>DD</sub> =Max.,	A,A1	25	20	mA
	Supply Current	$IOUT = 0 \text{ mA}, f = f_{MAX}$	A2,A3	30	25	
lcc1	Operating Supply	VDD=Max.,	A,A1	7	7	mA
	Current	IOUT = 0  mA, f = 0	A2,A3	7	7	
ISB1	TTL Standby Current	VDD=Max.,	A,A1	0.6	0.6	mA
	(TTLInputs)		A2,A3 <b>OR</b>	0.6	0.6	
	ULB Control	$\frac{V_{DD}=Max., V_{IN}=V_{IH} \text{ or }}{\overline{CS1}=V_{IL}, f=0, \overline{UB}=V_{I}}$				
ISB2	CMOS Standby	V <sub>DD</sub> =Max.,	A,A1	15	15	μA
	Current (CMOS Inputs)	$\overline{\text{CS1}} \ge V_{DD} - 0.2V$ ,	A2	25	25	•
	, ,	$CS2 \leq 0.2V,$ $V_{IN} \geq V_{DD} - 0.2V, or$ $V_{IN} \leq 0.2V, f = 0$	A3	65	65	
	ULB Control	V <sub>DD</sub> = Max., <del>CS1</del> = V <sub>IN</sub> ≤0.2V,f=0; <del>UB</del> /LE				

<sup>1.</sup> At  $f = f_{MAX}$ , address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.



#### **AC TEST CONDITIONS**

Parameter	65WV12816ALL (Unit)	65WV12816BLL (Unit)	
Input Pulse Level	0.4V to VDD-0.2V	0.4V to VDD-0.3V	
Input Rise and Fall Times	5 ns	5ns	
Input and Output Timing and Reference Level	VREF	Vref	
Output Load	See Figures 1 and 2	See Figures 1 and 2	

	65WV12816ALL (1.65V-2.2V)	65WV12816BLL (2.5V - 3.6V)
R1(Ω)	3070	3070
R2(Ω)	3150	3150
VREF	0.9V	1.5V
<b>V</b> TM	1.8V	2.8V

## **AC TEST LOADS**

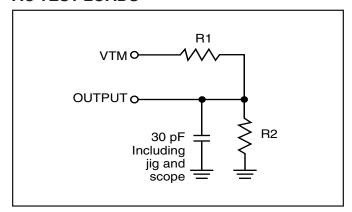


Figure 1

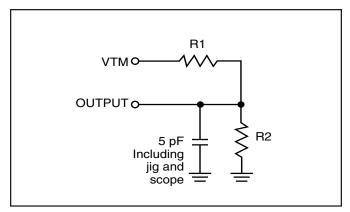


Figure 2



# READ CYCLE SWITCHING CHARACTERISTICS<sup>(1)</sup> (Over Operating Range)

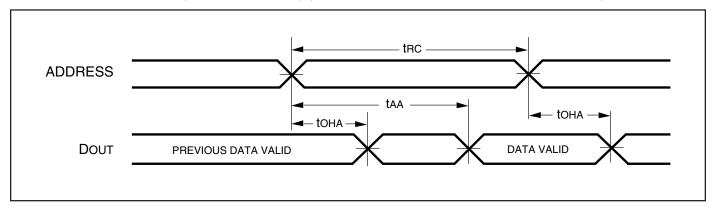
		-55	ns	-70 ns			
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
trc	Read Cycle Time	55	_	70	_	ns	
taa	Address Access Time	_	55	_	70	ns	
tона	Output Hold Time	10	_	10	_	ns	
tacs1/tacs2	CS1/CS2 Access Time	_	55	_	70	ns	
tdoe	OE Access Time	_	25	_	35	ns	
thzoe <sup>(2)</sup>	OE to High-Z Output	_	20	_	25	ns	
tLZOE <sup>(2)</sup>	OE to Low-Z Output	5	_	5	_	ns	
thzcs1/thzcs2 <sup>(2)</sup>	CS1/CS2 to High-Z Output	0	20	0	25	ns	
tLZCS1/tLZCS2 <sup>(2)</sup>	CS1/CS2 to Low-Z Output	10	_	10	_	ns	
<b>t</b> BA	LB, UB Access Time	_	55	_	70	ns	
tнzв	LB, UB to High-Z Output	0	20	0	25	ns	
<b>t</b> LZB	LB, UB to Low-Z Output	0	_	0	_	ns	

<sup>1.</sup> Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V, input pulse levels of 0.4 to 1.4V and output loading specified in Figure 1.

<sup>2.</sup> Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

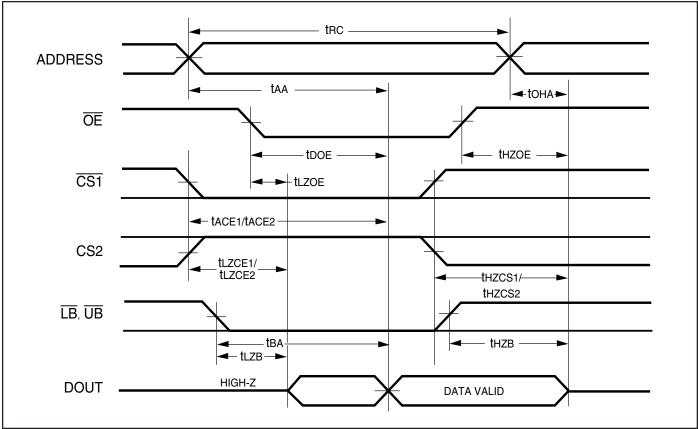


**READ CYCLE NO.**  $1^{(1,2)}$  (Address Controlled) ( $\overline{CS1} = \overline{OE} = V_{IL}$ ,  $\overline{CS2} = \overline{WE} = V_{IH}$ ,  $\overline{UB}$  or  $\overline{LB} = V_{IL}$ )



#### **AC WAVEFORMS**

READ CYCLE NO. 2<sup>(1,3)</sup> (CS1, CS2, OE, AND UB/LB Controlled)



- 1. WE is HIGH for a Read Cycle.
- 2. The device is continuously selected.  $\overline{OE}$ ,  $\overline{CS1}$ ,  $\overline{UB}$ , or  $\overline{LB} = V_{IL}$ .  $CS2 = \overline{WE} = V_{IH}$ .
- 3. Address is valid prior to or coincident with CS1 LOW transition.



# WRITE CYCLE SWITCHING CHARACTERISTICS(1,2) (Over Operating Range)

		-55	ns	-70	ns	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
twc	Write Cycle Time	55	_	70	_	ns
tscs1/tscs2	CS1/CS2 to Write End	45	_	60	_	ns
taw	Address Setup Time to Write End	45	_	60	_	ns
<b>t</b> HA	Address Hold from Write End	0	_	0	_	ns
<b>t</b> sa	Address Setup Time	0	_	0	_	ns
<b>t</b> PWB	LB, UB Valid to End of Write	45	_	60	_	ns
<b>t</b> PWE	WE Pulse Width	40	_	50	_	ns
tsd	Data Setup to Write End	25	_	30	_	ns
tho	Data Hold from Write End	0	_	0	_	ns
thzwe <sup>(3)</sup>	WE LOW to High-Z Output	_	20	_	20	ns
tLZWE <sup>(3)</sup>	WE HIGH to Low-Z Output	5	_	5	_	ns

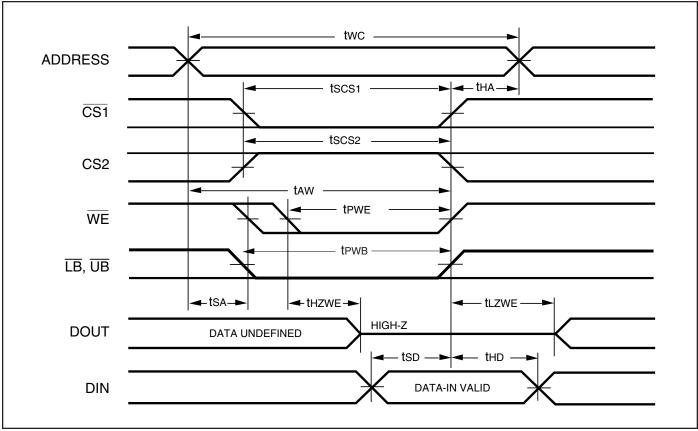
<sup>1.</sup> Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V, input pulse levels of 0.4V to 1.4V and output loading specified in Figure 1.

<sup>2.</sup> The internal write time is defined by the overlap of  $\overline{\textbf{CS1}}$  LOW, CS2 HIGH and  $\overline{\textbf{UB}}$  or  $\overline{\textbf{LB}}$ , and  $\overline{\textbf{WE}}$  LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.

3. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.



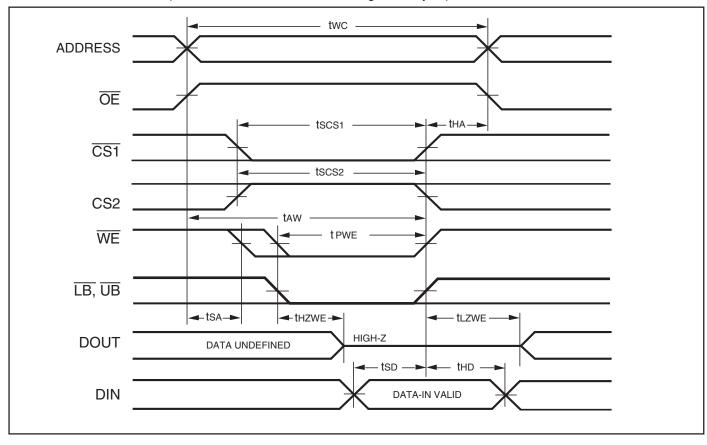
WRITE CYCLE NO.  $1^{(1,2)}$  ( $\overline{CS1}$  Controlled,  $\overline{OE}$  = HIGH or LOW)



- 1. WRITE is an internally generated signal asserted during an overlap of the LOW states on the  $\overline{\text{CS1}}$ , CS2 and  $\overline{\text{WE}}$  inputs and at least one of the  $\overline{\text{LB}}$  and  $\overline{\text{UB}}$  inputs being in the LOW state.
- 2. WRITE =  $(\overline{CS1})$  [  $(\overline{LB})$  =  $(\overline{UB})$  ]  $(\overline{WE})$ .

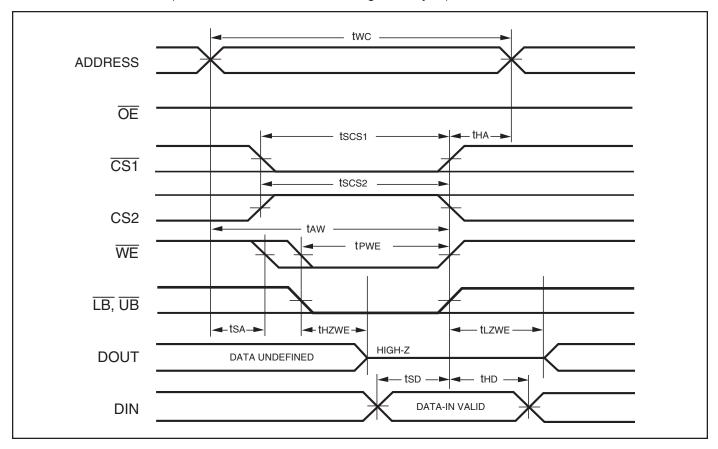


# WRITE CYCLE NO. 2 (WE Controlled: OE is HIGH During Write Cycle)



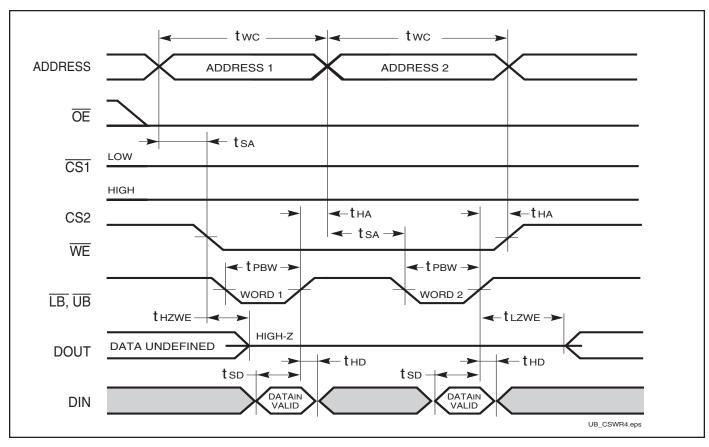


WRITE CYCLE NO. 3 (WE Controlled: OE is LOW During Write Cycle)





# AC WAVEFORMS WRITE CYCLE NO. 4 (UB/LB Controlled)



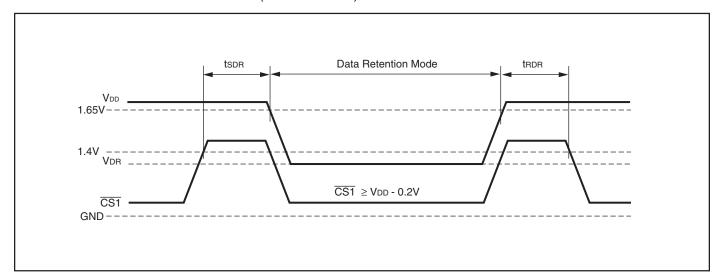


# **DATA RETENTION SWITCHING CHARACTERISTICS (LL)**

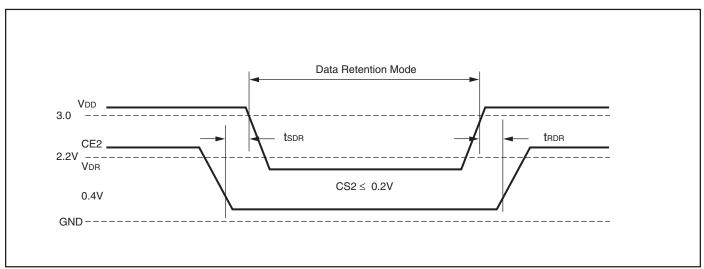
Symbol	Parameter	Test Condition	Options	Min.	Typ. <sup>(1)</sup>	Max.	Unit
VDR	VDD for Data Retention	See Data Retention Waveform		1.2	_	3.6	V
IDR	Data Retention Current	$Vdd = 1.2V, \overline{CS1} \ge VDD - 0.2V$	A, A1	_	5	15	μA
			A2	_	_	25	
			A3	_	_	65	
tsdr	Data Retention Setup Time	See Data Retention Waveform		0	_	_	ns
<b>t</b> rdr	Recovery Time	See Data Retention Waveform		trc	_	_	ns

**Note 1**: Typical values are measured at  $V_{DD} = 3.0V$ ,  $T_A = 25^{\circ}C$  and not 100% tested.

# DATA RETENTION WAVEFORM (CS1 Controlled)



# DATA RETENTION WAVEFORM (CS2 Controlled)





#### **ORDERING INFORMATION**

# IS65WV12816ALL (1.65V - 2.2V)

Temperature Range (A): 0°C to +70°C

Speed (ns)	Order Part No.	Package
70	IS65WV12816ALL-70TA	TSOP
	IS65WV12816ALL-70BA	mini BGA (6mm x 8mm)
	IS65WV12816ALL-70B2A	mini BGA (6mm x 8mm), 2 CS Option

## Temperature Range (A1): -40°C to +85°C

Speed (ns)	Order Part No.	Package
70	IS65WV12816ALL-70TA1	TSOP
	IS65WV12816ALL-70BA1	mini BGA (6mm x 8mm)
	IS65WV12816ALL-70B2A1	mini BGA (6mm x 8mm), 2 CS Option

# Temperature Range (A2): -40°C to +105°C

Speed (ns)	Order Part No.	Package
70	IS65WV12816ALL-70TA2	TSOP
	IS65WV12816ALL-70BA2	mini BGA (6mm x 8mm)
	IS65WV12816ALL-70B2A2	mini BGA (6mm x 8mm), 2 CS Option

## Temperature Range (A3): -40°C to +125°C

Speed (ns)	Order Part No.	Package
70	IS65WV12816ALL-70TA3	TSOP
	IS65WV12816ALL-70BA3	mini BGA (6mm x 8mm)
	IS65WV12816ALL-70B2A3	mini BGA (6mm x 8mm), 2 CS Option



#### **ORDERING INFORMATION**

# IS65WV12816BLL (2.5V - 3.6V)

Temperature Range (A): 0°C to +70°C

Speed (ns)	Order Part No.	Package
55	IS65WV12816BLL-55TA	TSOP
	IS65WV12816BLL-55BA	mini BGA (6mm x 8mm)
	IS65WV12816BLL-55B2A	mini BGA (6mm x 8mm), 2 CS Option
70	IS65WV12816BLL-70TA	TSOP
	IS65WV12816BLL-70BA	mini BGA (6mm x 8mm)
	IS65WV12816BLL-70B2A	mini BGA (6mm x 8mm), 2 CS Option

# Temperature Range (A1): -40°C to +85°C

Speed (ns)	Order Part No.	Package
55	IS65WV12816BLL-55TA1	TSOP
	IS65WV12816BLL-55BA1	mini BGA (6mm x 8mm)
	IS65WV12816BLL-55B2A1	mini BGA (6mm x 8mm), 2 CS Option
70	IS65WV12816BLL-70TA1	TSOP
	IS65WV12816BLL-70BA1	mini BGA (6mm x 8mm)
	IS65WV12816BLL-70B2A1	mini BGA (6mm x 8mm), 2 CS Option



# **ORDERING INFORMATION (continual)**

# IS65WV12816BLL (2.5V - 3.6V)

TEMPERATURE RANGE (A2): -40°C TO +105°C

Speed (ns)	Order Part No.	Package
	IS65WV12816BLL-55TA2	TSOP
	IS65WV12816BLL-55BA2	mini BGA (6mm x 8mm)
	IS65WV12816BLL-55B2A2	mini BGA (6mm x 8mm), 2 CS Option
70	IS65WV12816BLL-70TA2	TSOP
	IS65WV12816BLL-70BA2	mini BGA (6mm x 8mm)
	IS65WV12816BLL-70B2A2	mini BGA (6mm x 8mm), 2 CS Option

# Temperature Range (A3): -40°C to +125°C

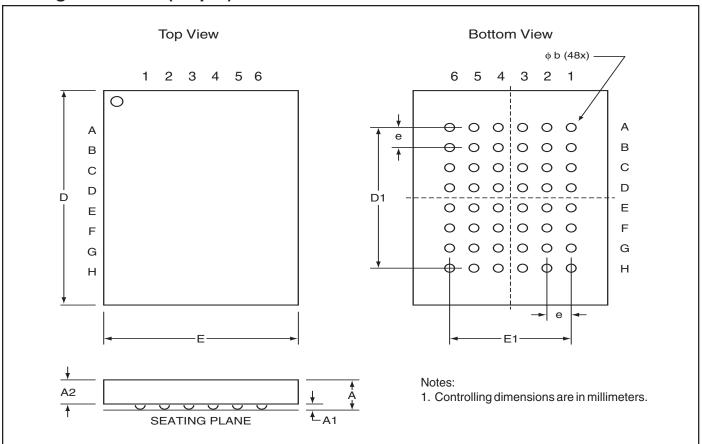
Speed (ns)	Order Part No.	Package
55	IS65WV12816BLL-55TA3 IS65WV12816BLL-55TLA3	TSOP TSOP, Lead-free
	IS65WV12816BLL-55BA3 IS65WV12816BLL-55BLA3	mini BGA (6mm x 8mm) mini BGA (6mm x 8mm), Lead-free
	IS65WV12816BLL-55B2A3	mini BGA (6mm x 8mm), 2 CS Option
70	IS65WV12816BLL-70TA3	TSOP
	IS65WV12816BLL-70BA3	mini BGA (6mm x 8mm)
	IS65WV12816BLL-70B2A3	mini BGA (6mm x 8mm), 2 CS Option

# PACKAGING INFORMATION



**Mini Ball Grid Array** 

Package Code: B (48-pin)



#### mBGA - 6mm x 8mm

	MILL	IMET	ERS	IN	INCHES			
Sym.	Min.	Тур.	Max.	Min.	Тур.	Max.		
N0. Leads		48						
Α	_	_	1.20		_	0.047		
A1	0.24	_	0.30	0.009	_	0.012		
A2	0.60	_	_	0.024	_	_		
D	7.90	_	8.10	0.311		0.319		
D1	5	.25 BS	С	0.:	207 B	SC		
E	5.90	_	6.10	0.232	_	0.240		
E1	3	.75 BS	С	0.	0.232 — 0.240 0.148 BSC			
е	0	.75 BS	С	0.0	030 B	SC		
b	0.30	0.35	0.40	0.012	0.014	0.016		

## mBGA - 8mm x 10mm

	MILLIMETER			INCHES			
Sym.	Min.	Тур.	Max.	Min.	Тур.	Max.	
N0.							
Leads		48					
Α	_	_	1.20	_	_	0.047	
A1	0.24		0.30	0.009		0.012	
A2	0.60	_	_	0.024	_	_	
D	9.90	_	10.10	0.390	_	0.398	
D1	5	.25 BS	С	0.2	207 BS	SC	
E	7.90	_	8.10	0.311	_	0.319	
E1	3	.75 BS	С	0.1	48 B	SC	
e	0.75 BSC			0.030 BSC			
b	0.30	0.35	0.40	0.012	0.014	4 0.016	

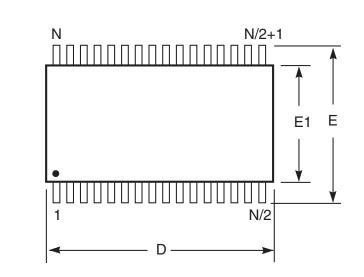
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# PACKAGING INFORMATION



**Plastic TSOP** 

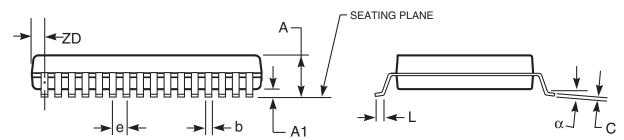
Package Code: T (Type II)



#### Notes:

- Controlling dimension: millimieters, unless otherwise specified.
- unless otherwise specified.

  BSC = Basic lead spacing between centers.
- Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.



	Plastic TSOP (T - Type II)											
	Millim	eters	Inche	s	Millim	eters	Inche	es	Millimeters		Inch	es
Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
Ref. Std.												
No. Leads	(N)	32				44	ļ				50	
Α	_	1.20	_	0.047	_	1.20	_	0.047	_	1.20	_	0.047
A1	0.05	0.15	0.002	0.006	0.05	0.15	0.002	0.006	0.05	0.15	0.002	0.006
b	0.30	0.52	0.012	0.020	0.30	0.45	0.012	0.018	0.30	0.45	0.012	0.018
С	0.12	0.21	0.005	0.008	0.12	0.21	0.005	0.008	0.12	0.21	0.005	0.008
D	20.82	21.08	0.820	0.830	18.31	18.52	0.721	0.729	20.82	21.08	0.820	0.830
E1	10.03	10.29	0.391	0.400	10.03	10.29	0.395	0.405	10.03	10.29	0.395	0.405
Е	11.56	11.96	0.451	0.466	11.56	11.96	0.455	0.471	11.56	11.96	0.455	0.471
е	1.27	BSC	0.050 I	BSC	0.80	BSC	0.032	BSC	0.80	BSC	0.031	BSC
L	0.40	0.60	0.016	0.024	0.41	0.60	0.016	0.024	0.40	0.60	0.016	0.024
ZD	0.95	REF	0.037	7 REF	0.81	REF	0.03	2 REF	0.88	REF	0.035	REF
α	0°	5°	0°	5°	0°	5°	0°	5°	0°	5°	0°	5°

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